

<b>Notic of References Cited</b>				Application No. <i>09-882289</i>		Applicant(s) <i>Wharner et al.</i>	
				Examiner <i>George Goudreau</i>		Group Art Unit <i>1763</i>	
						Page <i>1</i> of <i>1</i>	
U.S. PATENT DOCUMENTS							
★	DOCUMENT NO.	DATE	NAME			CLASS	SUBCLASS
A							
B							
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N	<i>51-145,267</i>	<i>12-14-76</i>	<i>Japan</i>	<i>Kawasaki et al.</i>			
O	<i>05-283,679</i>	<i>10-29-78</i>	<i>Japan</i>	<i>Kawasaki et al.</i>			
P							
Q							
R							
S							
T							
NON-PATENT DOCUMENTS							
★	DOCUMENT (Including Author, Title, Source, and Pertinent Pages)						DATE
U	<i>"Furnace Nitridation of Thermal Silicon In Pure Nitrogen Oxide Ambient For VLSI MOS Application";</i>						
W	<i>Ahn et al.; (1992); IEEE Electron Device Letters; 13(2); pp 117-119</i>						
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(See Manual of Patent Examining Procedure, Section 707.05(a).)